



LABORATOIRE ÉLECTRONIQUE,
Systèmes de Communication et
Microsystèmes



Low cost RoF solution development for Mobile Fronthaul networks

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Outline

- Introduction: MORF Project, FUI, March 2015
 - Context and goals
- OM RoF simulation tool
- OM quantities
- Behavioral model implementation
- RoF link Design simulation Analysis
- OM Individual performance extraction
- Conclusions and Perspectives

MORF – Multiplex OFDM Radio-over-Fiber

Centre de Commutation d'Infrastructure

PmP SYSTEM

Transmission Hub
or
Base station

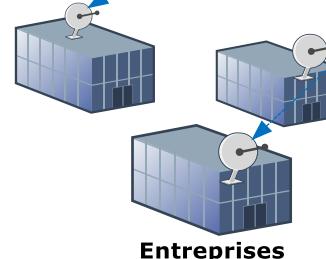
"FRONTHAUL MORF"



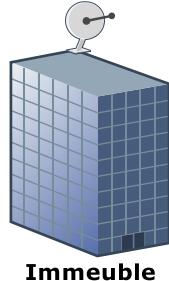
FO 10Km



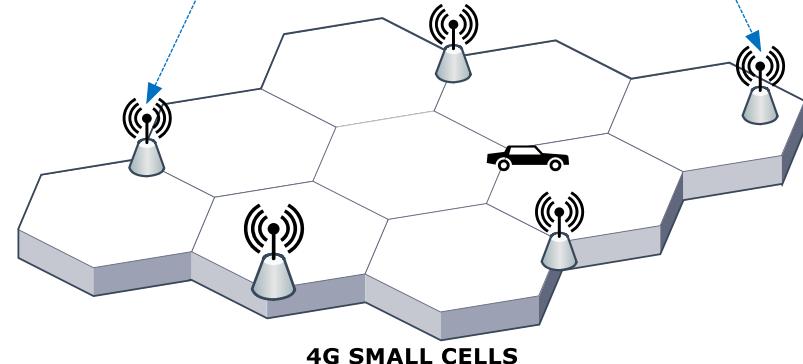
CCI



Entreprises



Immeuble

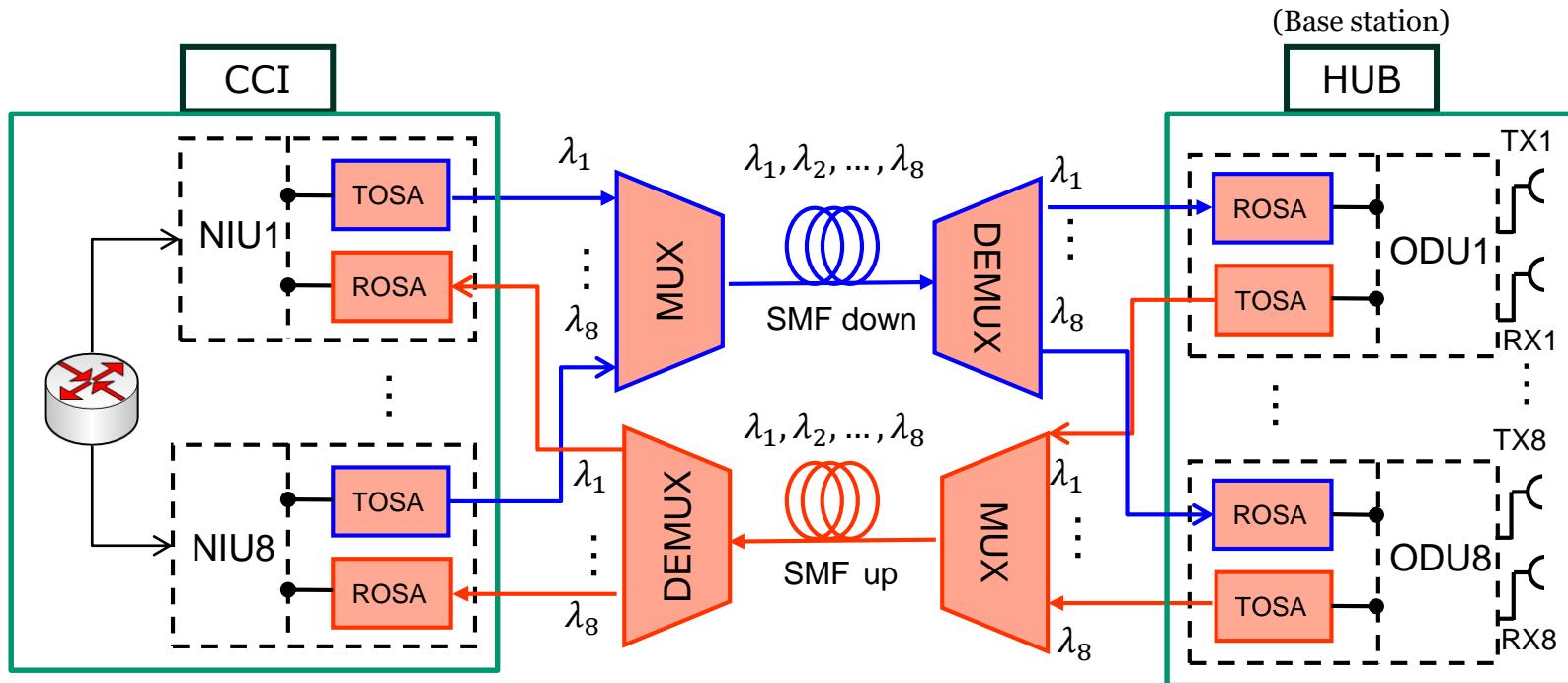


4G SMALL CELLS

- RoF Technology over 10 to 20km
- Bidirectional optical links carrying OFDM multiplex channels
- Low cost base stations – data/signal processing centralized at the CCI
- Dark Fiber compatibility

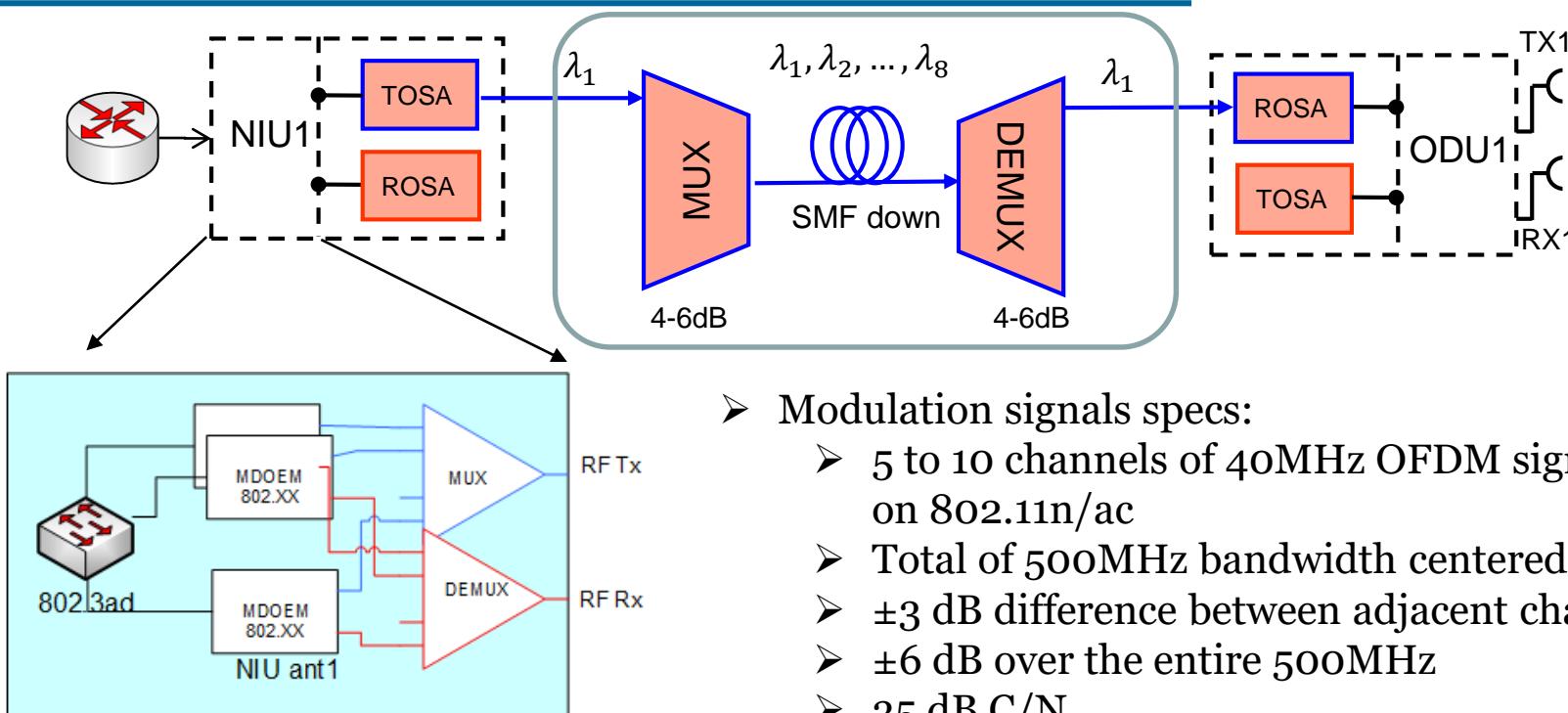
Point-to-Point Architecture

TOSA – Transmitter Optical Sub-Assembly
ROSA – Receiver Optical Sub-Assembly
WDM – Wavelength Division Multiplexing



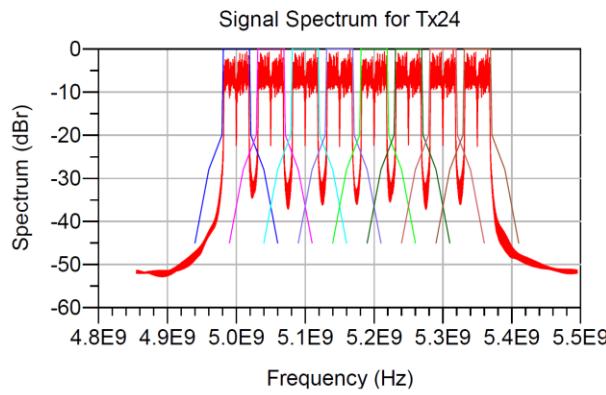
- 4 to 8 INU/ODU in order to implement 4-8 radiocells
- Integration of the TOSA and ROSA modules and the implementation of the WDM

Point-to-Point Architecture



- Modulation signals specs:
 - 5 to 10 channels of 40MHz OFDM signals Based on 802.11n/ac
 - Total of 500MHz bandwidth centered at 5-6GHz
 - ± 3 dB difference between adjacent channels
 - ± 6 dB over the entire 500MHz
 - 35 dB C/N

- RoF Link:
 - SMF link at $1.55\mu\text{m}$
 - Up to 22dB optical losses (20km, connectors, mux/demux, ..)
 - Bandwidth of 6GHz
 - 37 dB C/N, 1.5% EVM
 - Asymmetric available power: Down/Up load link



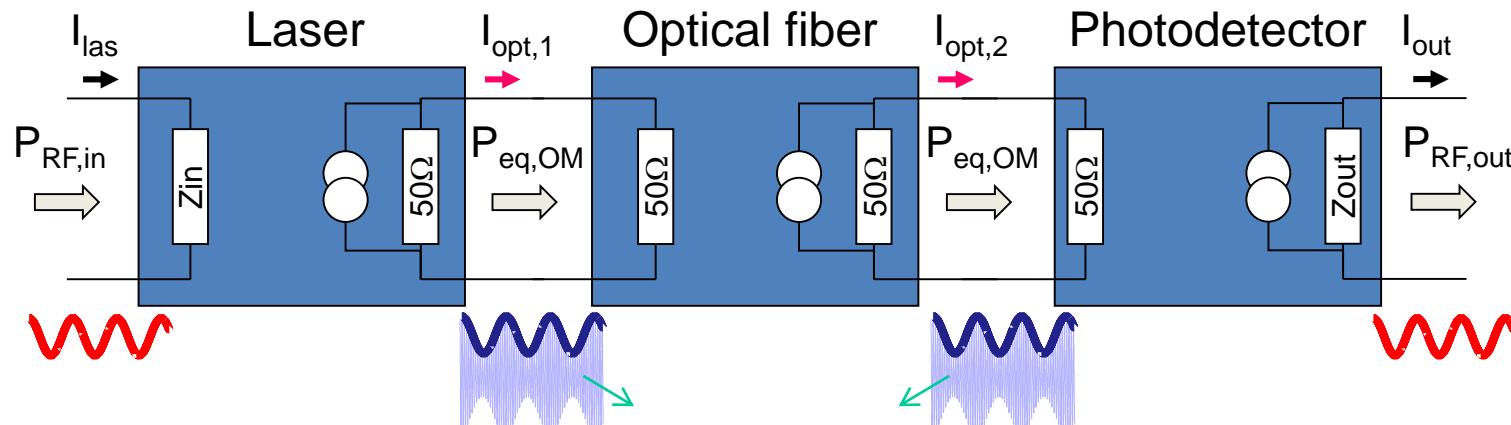
OM RoF simulation tool
OM quantities
Behavioral model implementation
RoF link Design simulation Analysis
OM Individual performance extraction

OM quantities Electronic/Photonic conversion

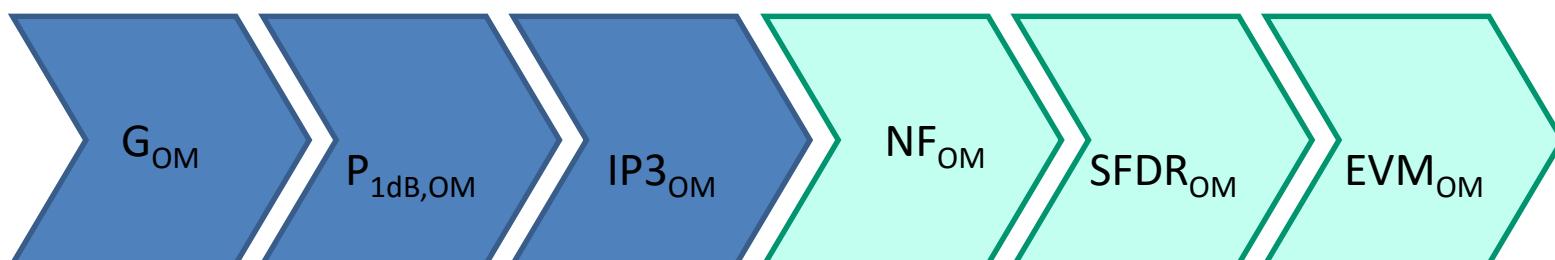
- Equivalent opto-microwave power

$$I_{opt} = \frac{1}{W} \cdot P_{opt}$$

$$P_{eq,OM} = \frac{1}{2} \cdot R_0 \cdot I_{opt}^2 = \frac{1}{2} \cdot R_0 \cdot \left(\frac{1}{W} \cdot P_{opt} \right)^2$$



As probed by a 1A/W (normalized)
reference photodiode loaded by 50Ohms



OM quantities

With equivalent opto-microwave power:

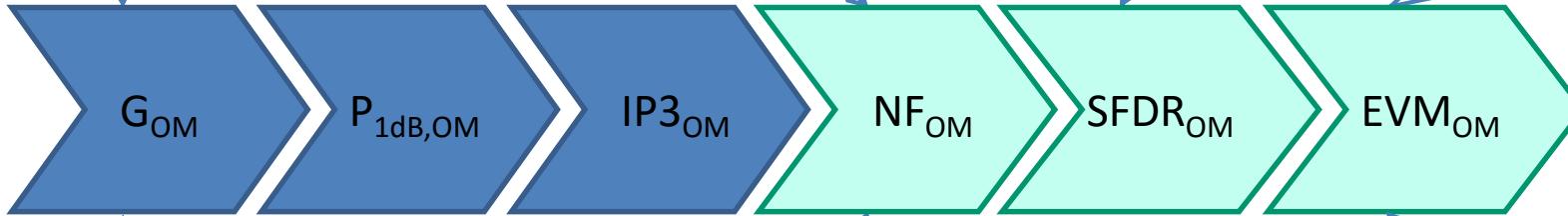
- $OIP3_{OM}$ and $OP1dB_{OM}$ for the laser & optical parts
- $IIP3_{OM}$ and $IP1dB_{OM}$ for the photodiode & optical parts
- P1dB and IP3 systems relation

$$SFDR_{LD,PD}^{OM} \left[dB \cdot Hz^{\frac{2}{3}} \right] = \frac{2}{3} \left(OIP3_{LD,PD}^{OM} - N_{LD,PD}^{OUT,NOISE} \right)$$

$$G_{OM} = \frac{P_{out,eq,OM}}{Pin,available_{eq,OM}}$$

$$F_{LD,PD}^{OM} = \left. \frac{SNR_{in}^{OM}}{SNR_{out}^{OM}} \right|_{T_o}$$

$$EVM_{LD,PD}^{OM} [linear] = \sqrt{\frac{P_{error\ vector}^{OM}}{P_{reference}^{OM}}}$$

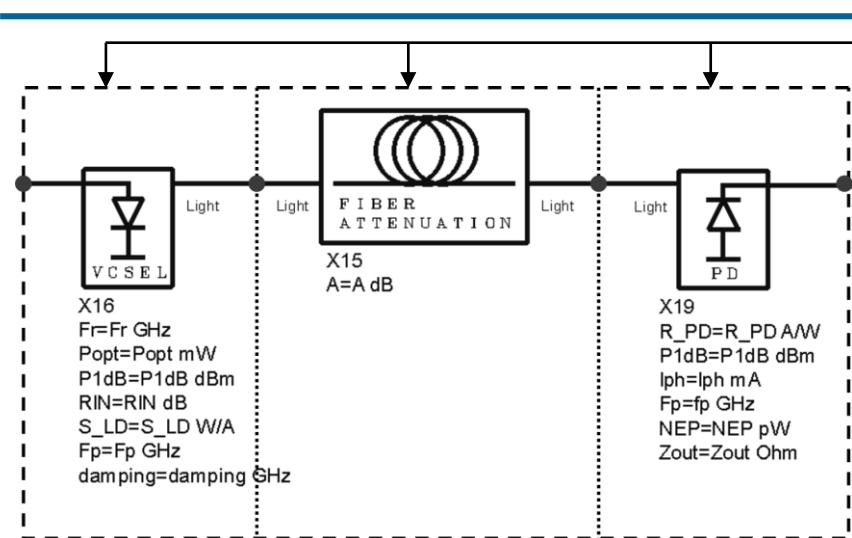


$$N_{ref,OM} = k \cdot T \cdot B$$

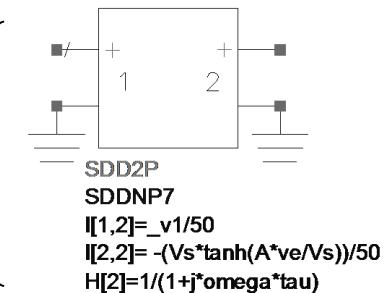
$$EVM_{LD,PD}^{OM} [dB] \approx 10 \log_{10} \left[B \cdot 10^{\frac{kT + NF_{LD,PD}^{OM} - P}{10}} + 10^{\frac{P - IIP3_{LD,PD}^{OM}}{5}} \right]$$

- Friis formula applicable
- $SFDR_{OM}$ for each individual parts
- EVM_{OM} impact
- Ready to be included into microwave CAD

OM behavior model implementation



SDD - Symbolically defined device

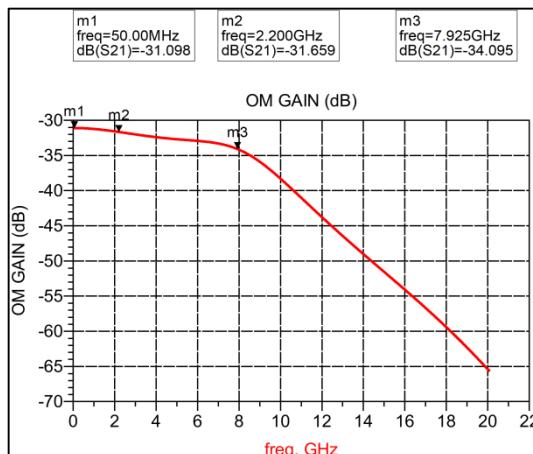


NL

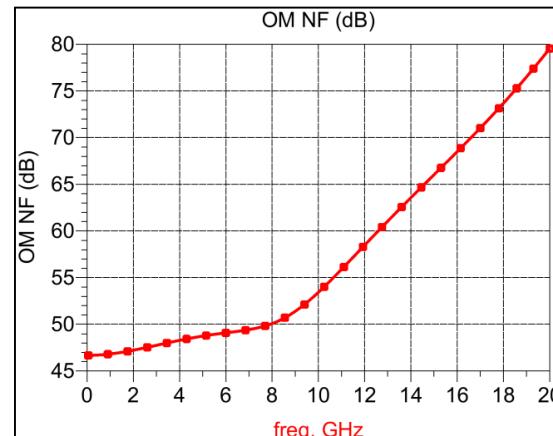
$$I_{out} = 2 \cdot I_S \cdot \tanh\left(\frac{G \cdot I_{in}}{I_S}\right) = 2 \cdot I_{opt}$$

NF

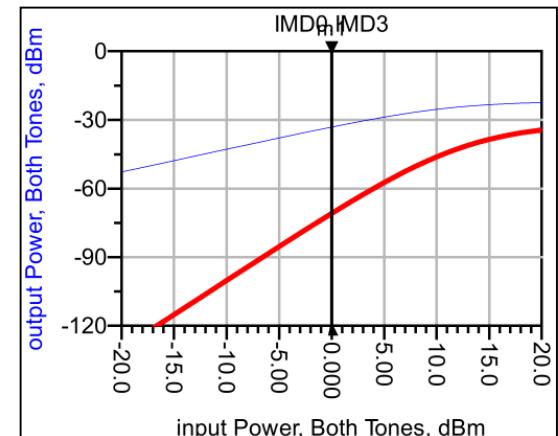
$$RIN(f) = A \cdot \frac{4\pi^2 \cdot f^2 + B}{16\pi^4 (f_r^2 - f^2)^2 + 4\pi^2 \cdot \gamma^2 \cdot f^2}$$



Frequency response

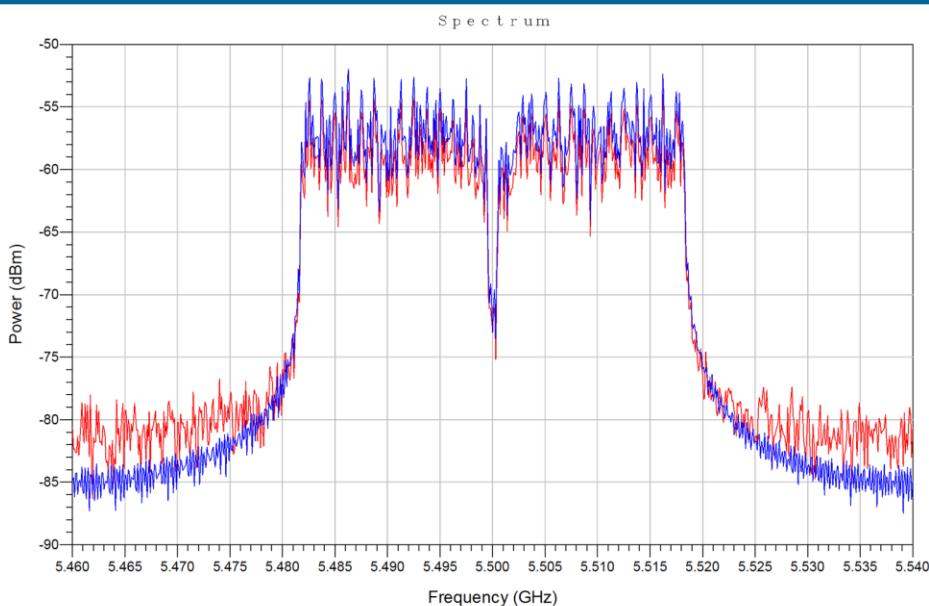


Noise Figure

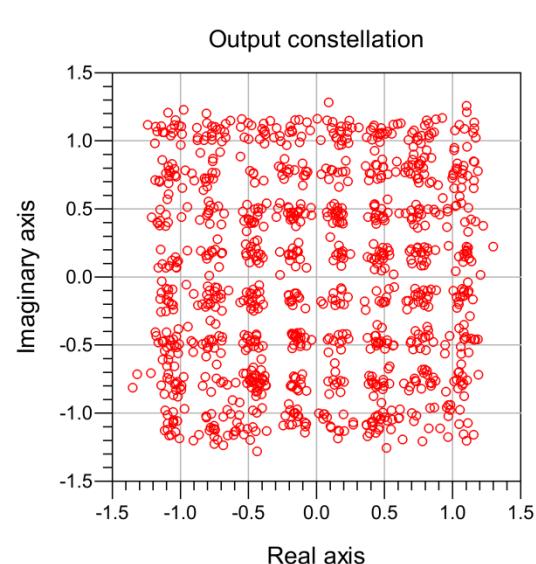
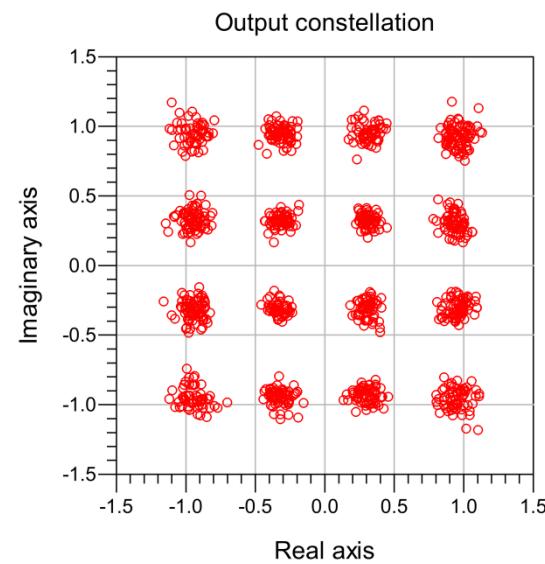
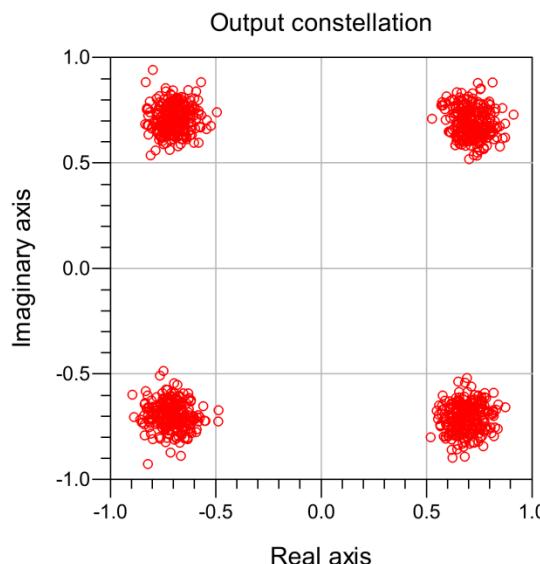


Nonlinearities

OM behavior model implementation

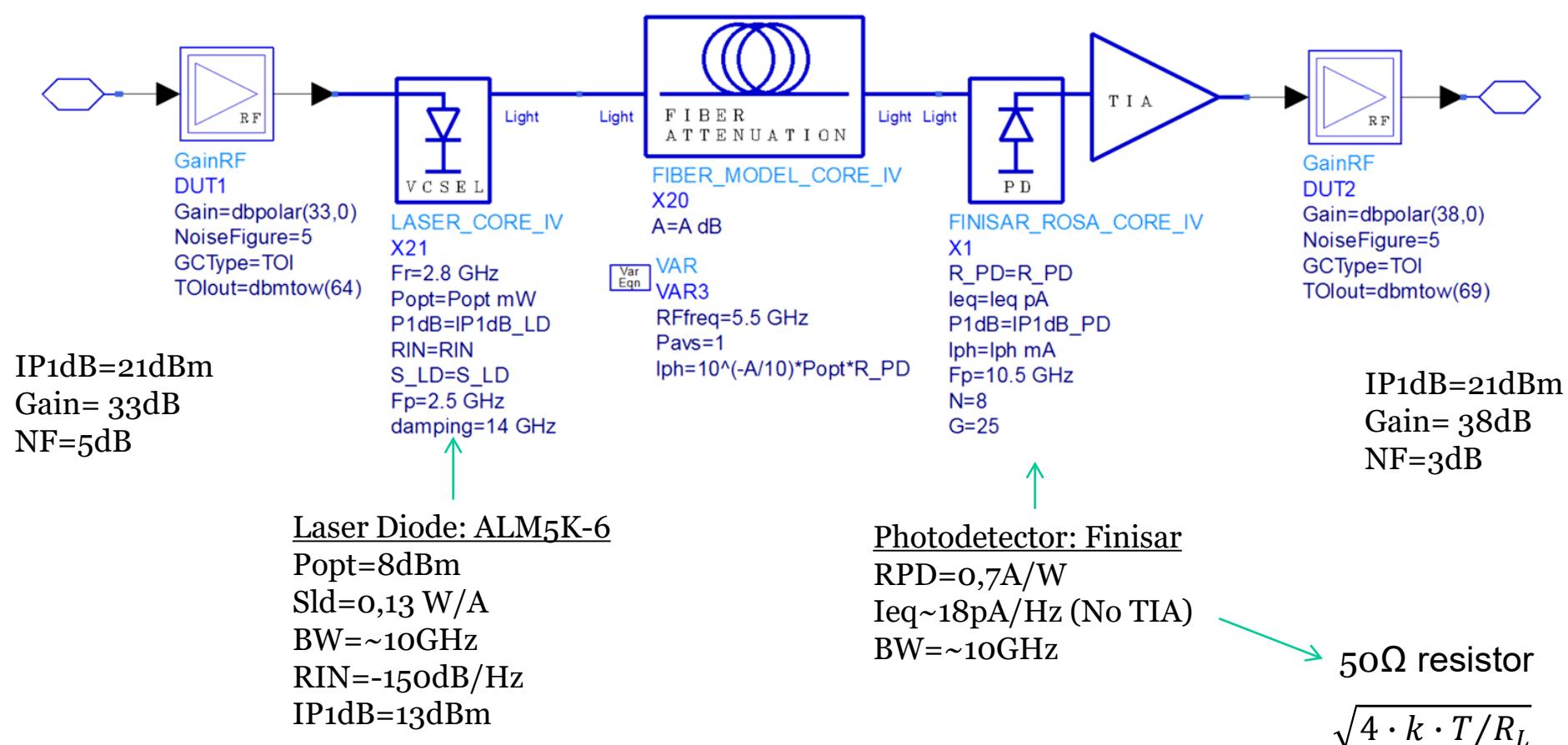


Signal Parameter	IEEE 802.11n OFDM PHY HT
Occupied bandwidth	33,75 MHz
Fs: OFDM Sampling rate	40 MHz
Number of subcarriers	128
FFT period (symbol duration)	3,2 μ m
Subcarrier spacing	312,5kHz
GI duration	0,4 μ s
OFDM symbol duration	3,6 μ s
Number of data subcarriers	108
Number of pilots subcarriers	6
Number of DC subcarriers	3
Modulation	QPSK 60Mbps 16-QAM 120Mbps 64-QAM 180Mbps



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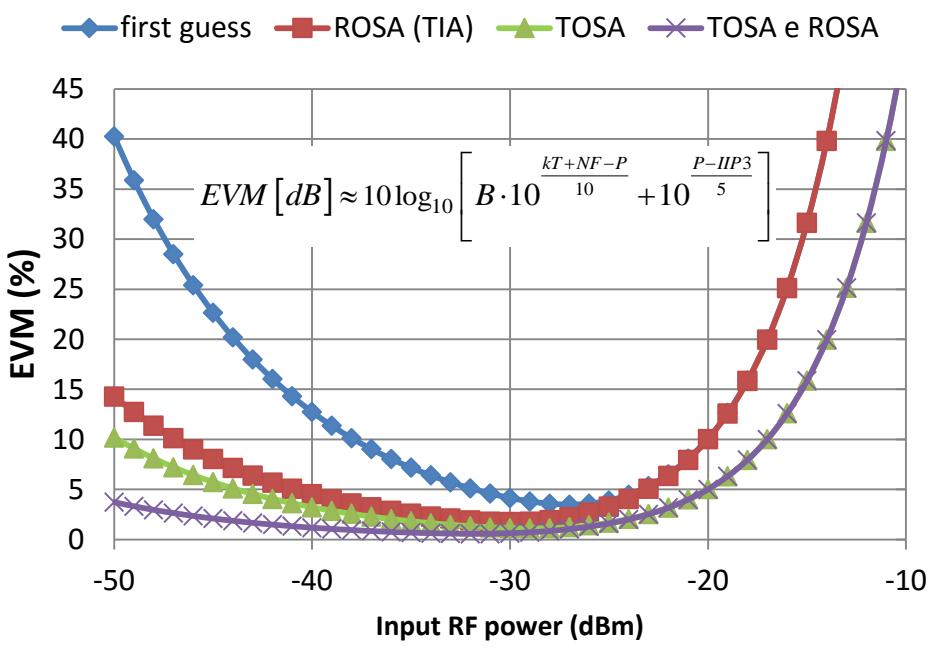
RoF link Design simulation Analysis: First guess



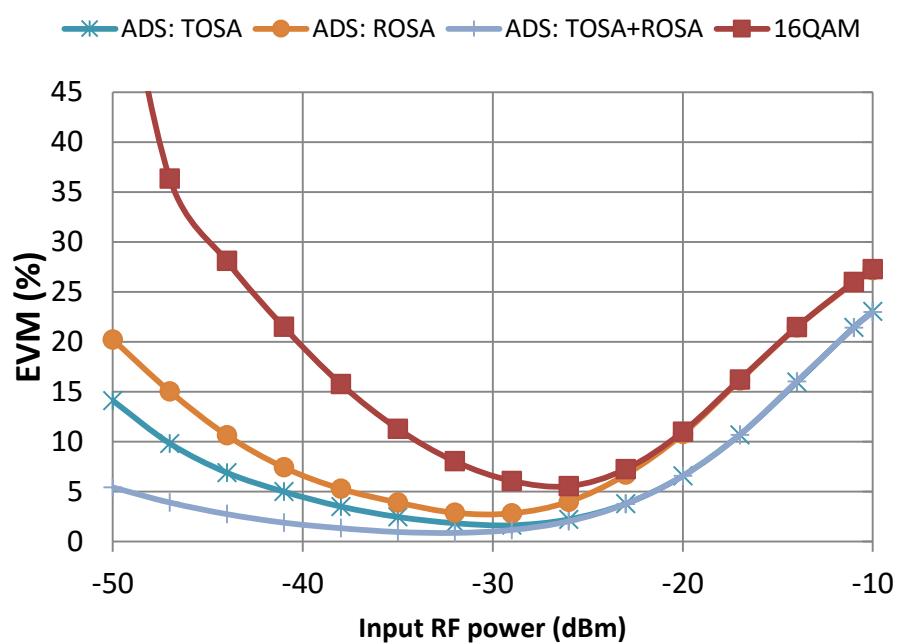
- Criteria:
 - 22dB optical losses (worst scenario)
 - Overall link gain of 0dB
 - Available Input power: -65 to -25 dBm

RoF link Design simulation Analysis: First guess

TOSA and ROSA performance impact: theoretical



TOSA and ROSA performance impact: ADS



SLD=0.13 to 0.5 W/A
IP1dB = 13 to 16 dBm
f3dB=8GHz
RIN=-150dB/Hz

Losses = 22 dB

RPD=0,7A/W
TI= 25 to 300Ω
Ieq=18 to 10pA/Hz
f3dB=10GHz

- Min EVM <1 % with input power of -32dBm

RoF link Design simulation Analysis:

$$EVM [dB] \approx 10 \log_{10} \left[B \cdot 10^{\frac{kT+NF-P}{10}} + 10^{\frac{P-IIP3}{5}} \right]$$

Advantage:

simple, fast, excel

Limitations

No Flexibility

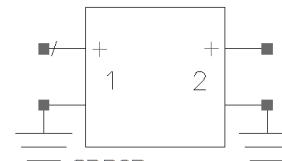
Modulation signal properties

PAPR

Schemes

...

Frequency response



$$\begin{aligned} I[1,2] &= v_1/50 \\ I[2,2] &= -(V_s * \tanh(A * v_e / V_s)) / 50 \\ H[2] &= 1 / (1 + j * \omega * \tau) \end{aligned}$$

Advantages:

Precise, flexible

Analogue properties:

Frequency response

Nonlinearities

Noise

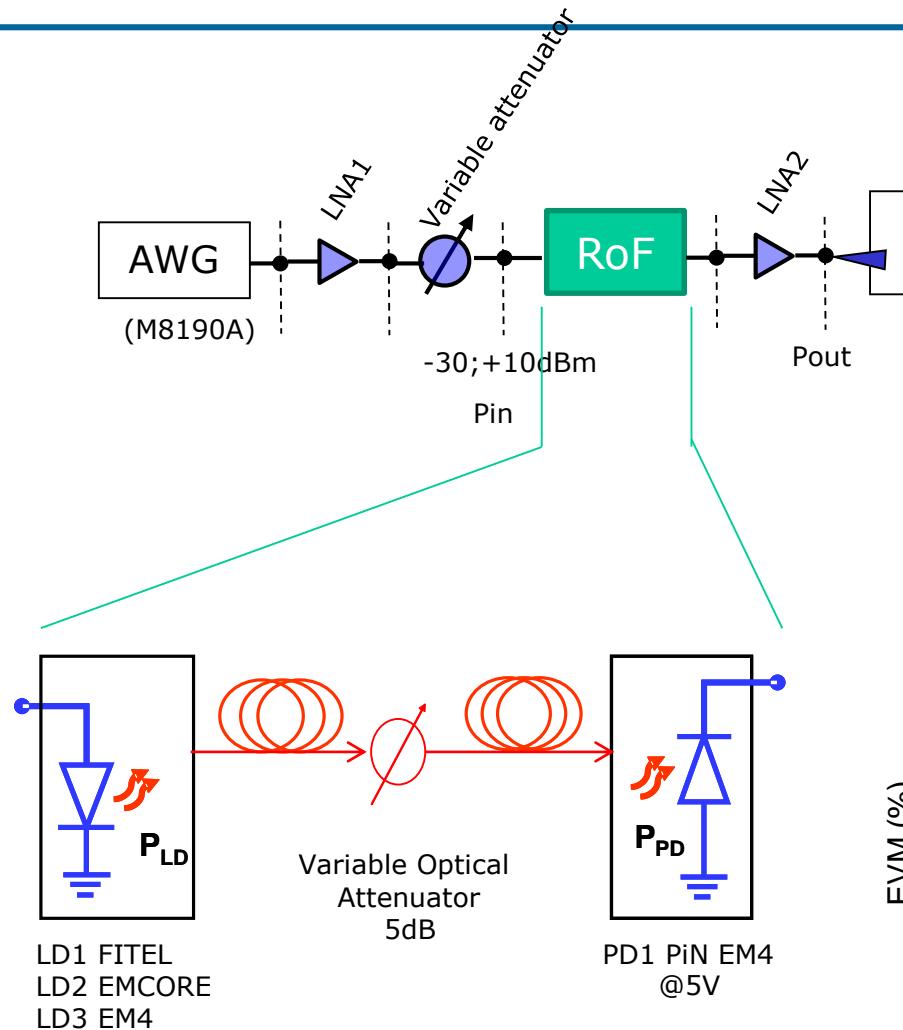
modulation signal properties

Limitations

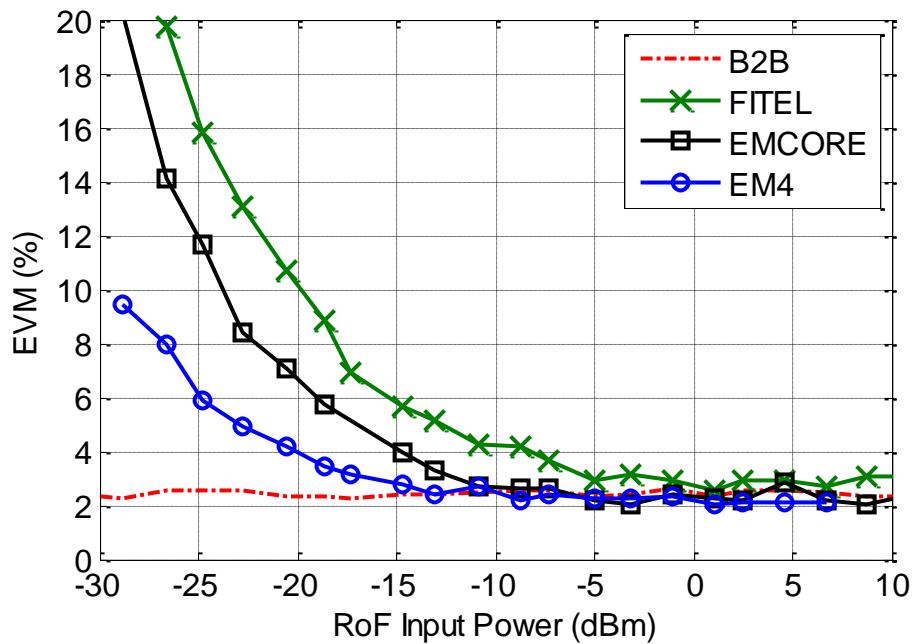
Nonlinear Memory-less model
(tanh, cann's,...)

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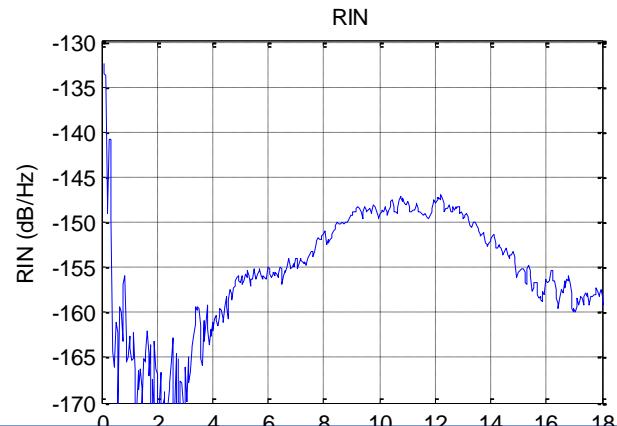
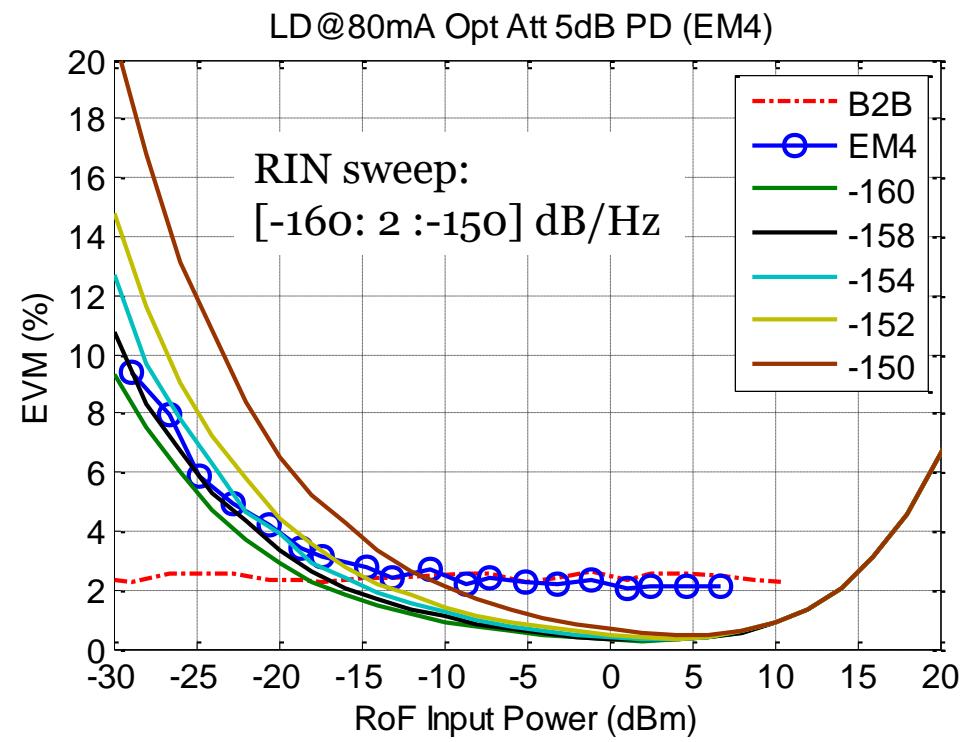
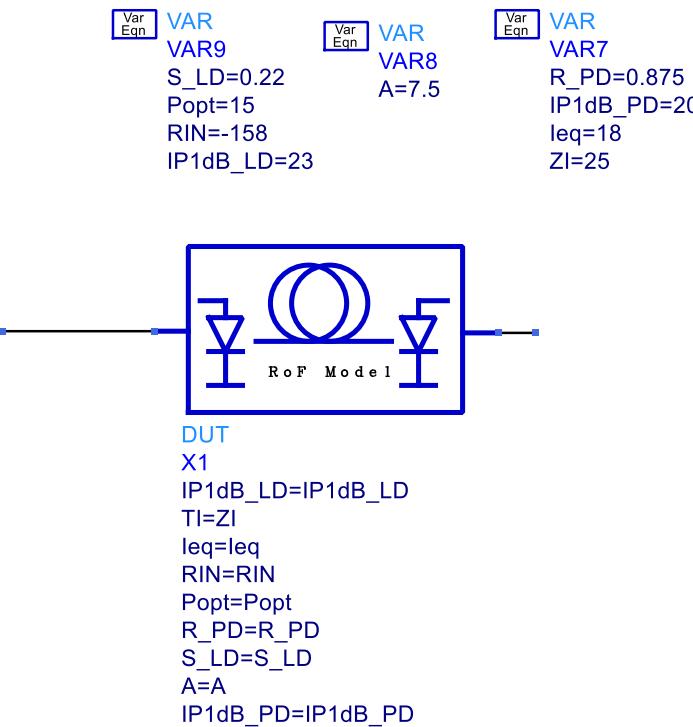
OM Individual performance extraction



Low cost lasers:
4GHz bandwidth



OM Individual performance extraction



- Back-to-back EVM avoided: min EVM=0.32% @ +3dBm
- RIN extracted to -158dB/Hz
- NL simulation

Conclusions and Perspectives

- **Conclusions:**
 - Low cost RoF solution development for Mobile Fronthaul networks
 - MORF project: IF-RoF, WDM
 - OM RoF simulation tool
 - Opto-microwave quantities defined: from GOM to EVMOM
 - Enable further optimization of devices individually
 - Optoelectronic behavioral model
 - Precise parameter extraction from EVM measurements
 - All microwave CAD tools enabled for optoelectronic devices and circuits
- **Perspectives and Extensions:**
 - Extending the application to more than one channel
 - Widening the implementation by extending to more than one sector.
 - Extended approach to implement on 802.11.ac (80 MHz per channel)
 - Nonlinear Memory-less mode development
 - Phase noise implementation

Merci !

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